

$V_{DSS}$	30V
$R_{DS(on)}(Max.)$	9.3m $\Omega$
$I_D$	$\pm 12A$
$P_D$	2W

### ●Features

- 1) Low on - resistance.
- 2) High Power Package (HSMT8).
- 3) Pb-free lead plating ; RoHS compliant.
- 4) Halogen Free.

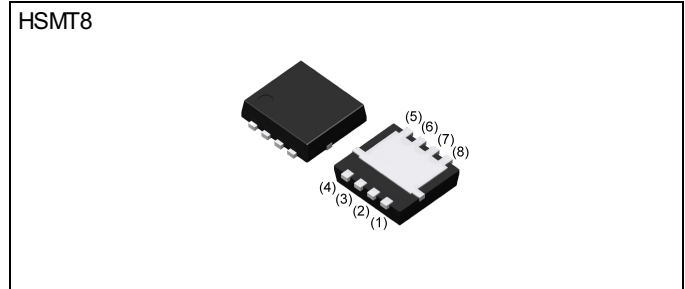
### ●Application

Switching

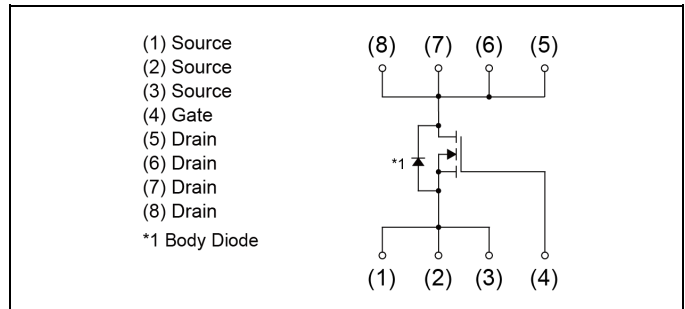
### ●Absolute maximum ratings ( $T_a = 25^\circ C$ )

Parameter	Symbol	Value	Unit
Drain - Source voltage	$V_{DSS}$	30	V
Continuous drain current	$I_D$	$\pm 12$	A
Pulsed drain current	$I_{D,pulse}^{*1}$	$\pm 48$	A
Gate - Source voltage	$V_{GSS}$	$\pm 20$	V
Power dissipation	$P_D^{*2}$	2	W
Junction temperature	$T_j$	150	$^\circ C$
Range of storage temperature	$T_{stg}$	-55 to +150	$^\circ C$

### ●Outline



### ●Inner circuit



### ●Packaging specifications

Type	Packing	Embossed Tape
	Reel size (mm)	330
	Tape width (mm)	12
	Basic ordering unit (pcs)	3000
	Taping code	TB
	Marking	E120BN

## ● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	$R_{thJA}^{*2}$	-	62.5	-	°C/W

● Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	30	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = 1mA$ referenced to $25^\circ\text{C}$	-	21	-	mV/°C
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	μA
Gate - Source leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	1.0	-	2.5	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	$I_D = 1mA$ referenced to $25^\circ\text{C}$	-	-3	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}^{*3}$	$V_{GS} = 10V, I_D = 12A$	-	6.6	9.3	mΩ
		$V_{GS} = 4.5V, I_D = 12A$	-	8.6	11.9	
Transconductance	$g_{fs}^{*3}$	$V_{DS} = 5V, I_D = 12A$	13	-	-	S

\*1  $P_w \leq 10\mu\text{s}$ , Duty cycle  $\leq 1\%$

\*2 Mounted on a ceramic board (30×30×0.8mm)

\*3 Pulsed

**● Electrical characteristics (T<sub>a</sub> = 25°C)**

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	1500	-	pF
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 15V	-	175	-	
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	140	-	
Turn - on delay time	t <sub>d(on)</sub> <sup>*3</sup>	V <sub>DD</sub> ≈ 15V, V <sub>GS</sub> = 10V	-	9	-	ns
Rise time	t <sub>r</sub> <sup>*3</sup>	I <sub>D</sub> = 6A	-	30	-	
Turn - off delay time	t <sub>d(off)</sub> <sup>*3</sup>	R <sub>L</sub> = 2.5Ω	-	46	-	
Fall time	t <sub>f</sub> <sup>*3</sup>	R <sub>G</sub> = 10Ω	-	12	-	

**● Gate charge characteristics (T<sub>a</sub> = 25°C)**

Parameter	Symbol	Conditions	Values			Unit	
			Min.	Typ.	Max.		
Total gate charge	Q <sub>g</sub> <sup>*3</sup>	V <sub>DD</sub> ≈ 15V I <sub>D</sub> = 12A	V <sub>GS</sub> = 10V	-	29	-	nC
Gate - Source charge	Q <sub>gs</sub> <sup>*3</sup>		V <sub>GS</sub> = 4.5V	-	14	-	
Gate - Drain charge	Q <sub>gd</sub> <sup>*3</sup>		V <sub>GS</sub> = 4.5V	-	3.3	-	
				-	4.7	-	

**● Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)**

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous forward current	I <sub>S</sub>	T <sub>a</sub> = 25°C	-	-	1.67	A
Body diode pulse current	I <sub>SP</sub> <sup>*1</sup>		-	-	48	
Forward voltage	V <sub>SD</sub> <sup>*3</sup>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.67A	-	-	1.2	V

● Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

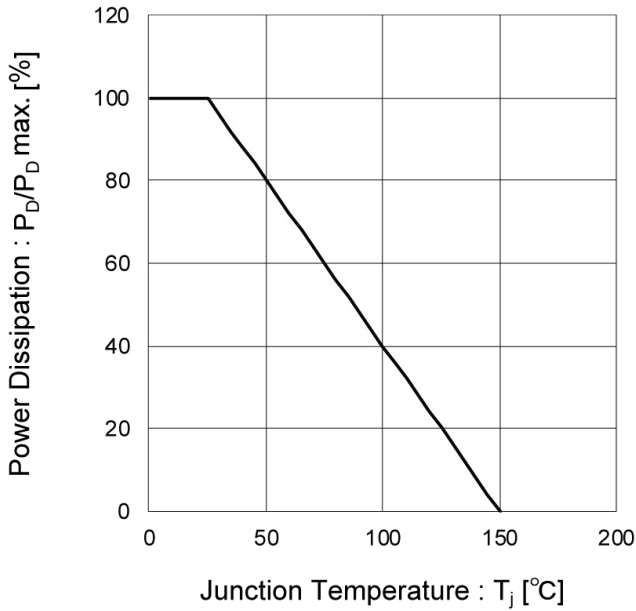


Fig.2 Maximum Safe Operating Area

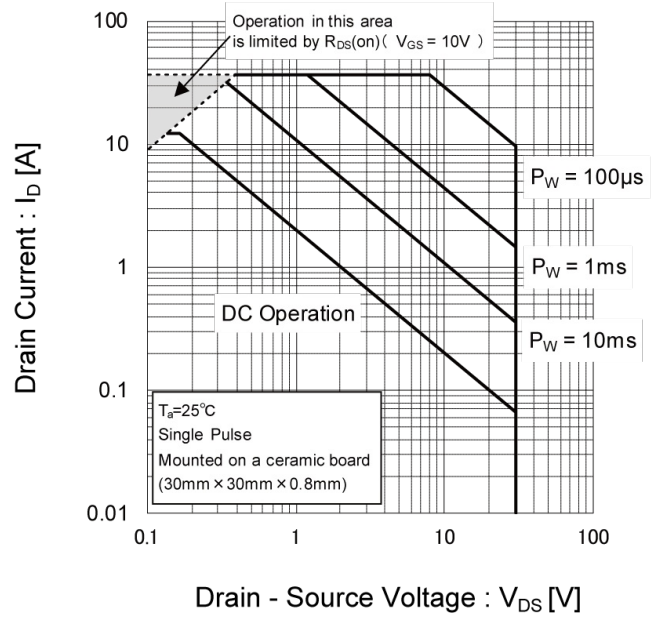


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

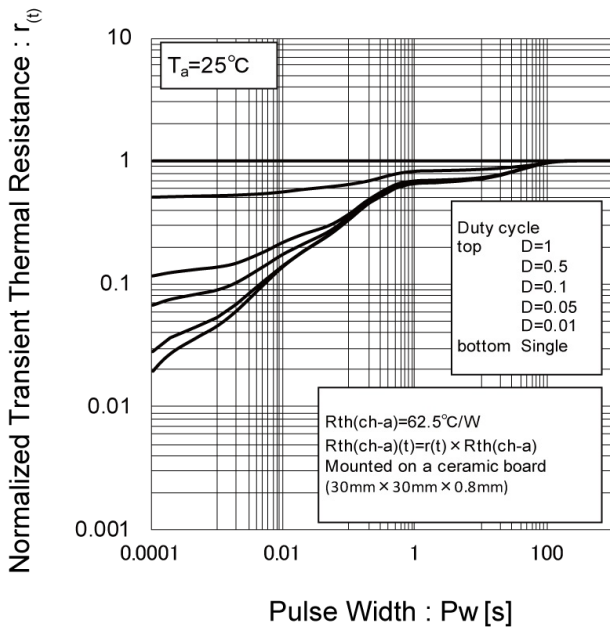
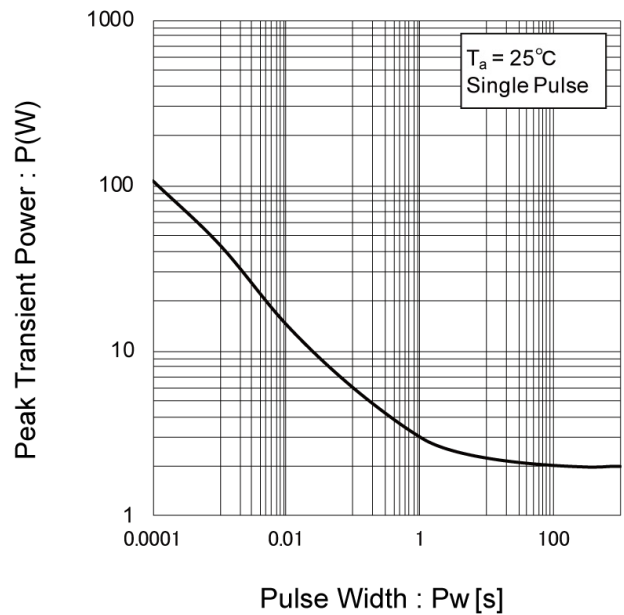


Fig.4 Single Pulse Maximum Power dissipation



● Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

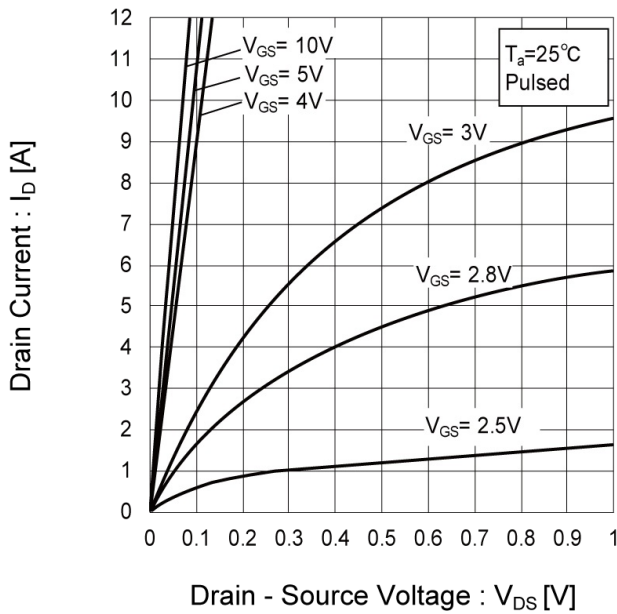


Fig.6 Typical Output Characteristics(II)

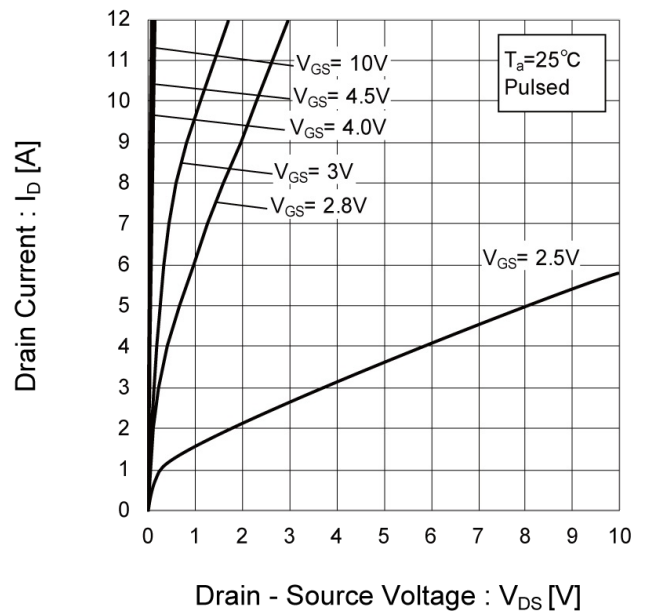
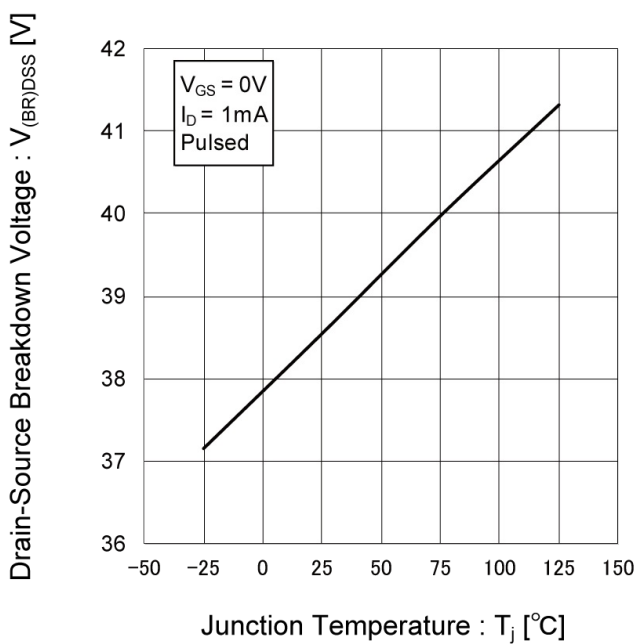


Fig.7 Breakdown Voltage vs. Junction Temperature



●Electrical characteristic curves

Fig.8 Typical Transfer Characteristics

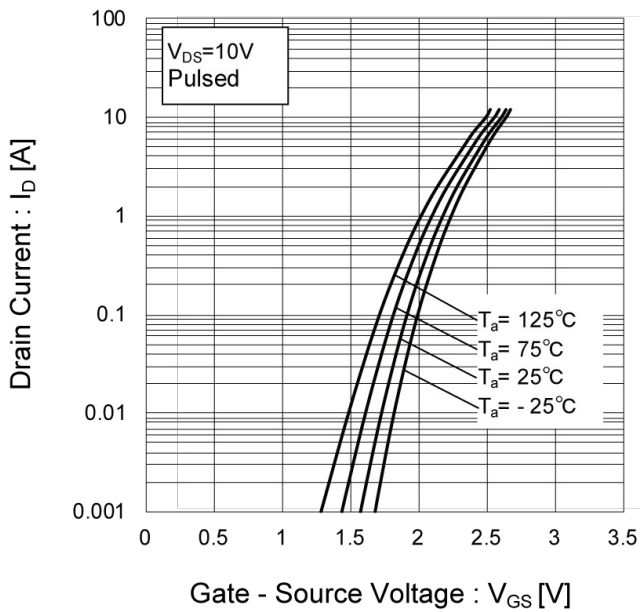


Fig.9 Gate Threshold Voltage vs. Junction Temperature

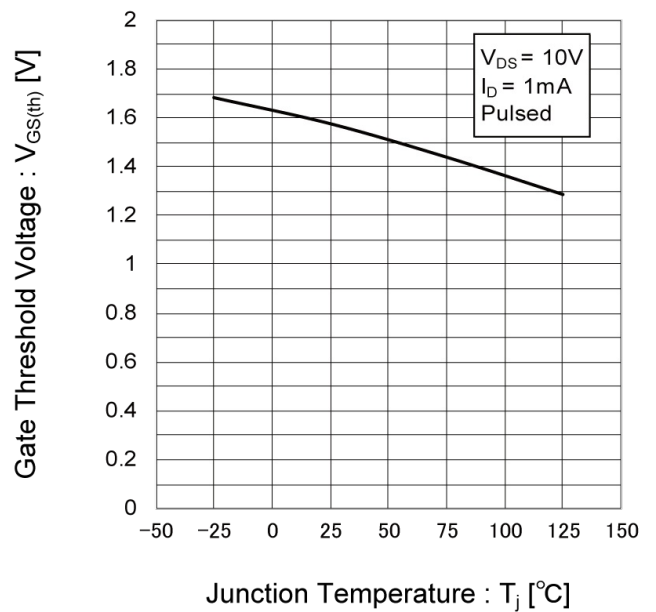
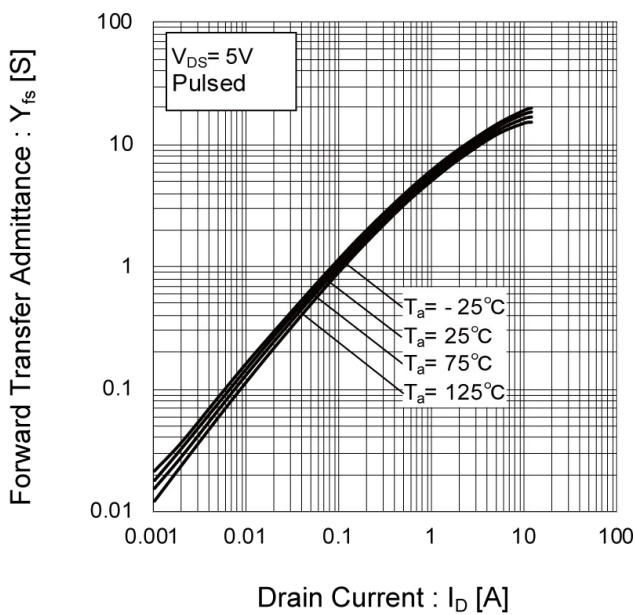


Fig.10 Transconductance vs. Drain Current



● Electrical characteristic curves

Fig.11 Drain Current Derating Curve

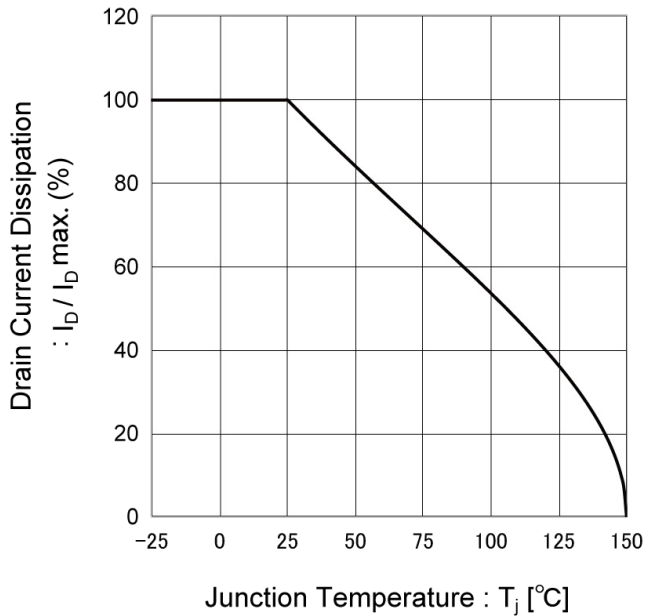


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

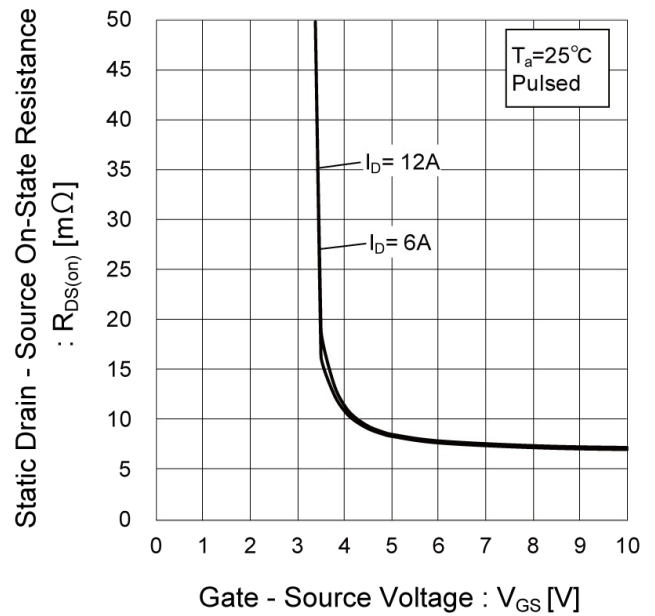
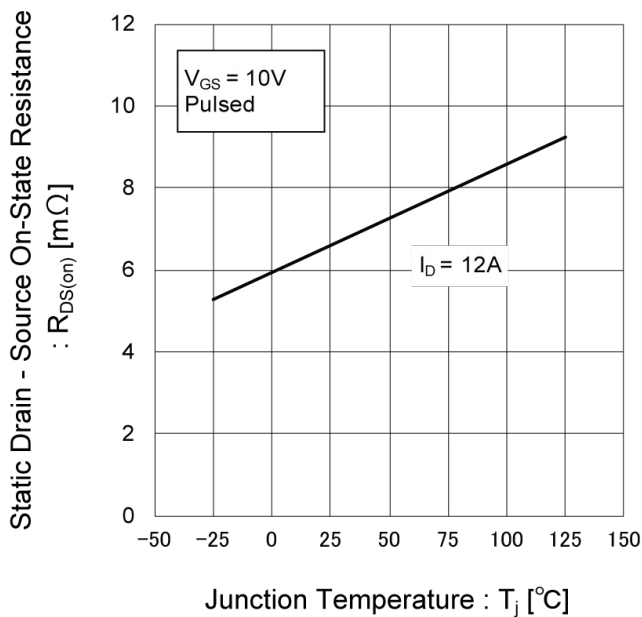


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature



● Electrical characteristic curves

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

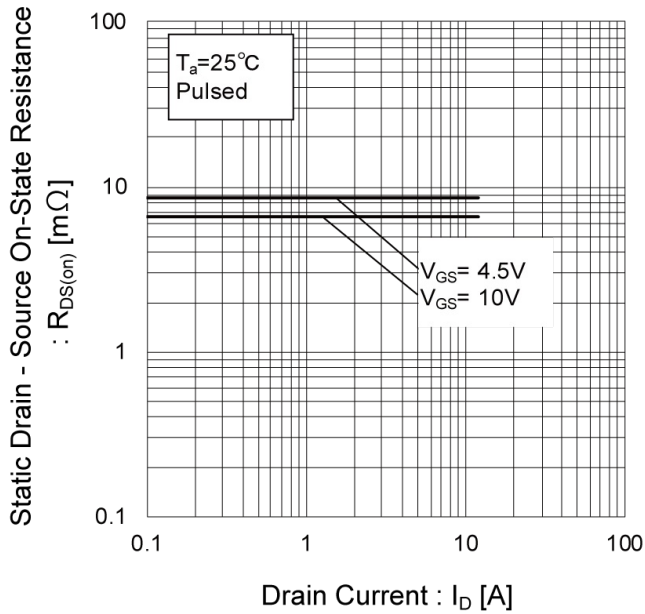


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

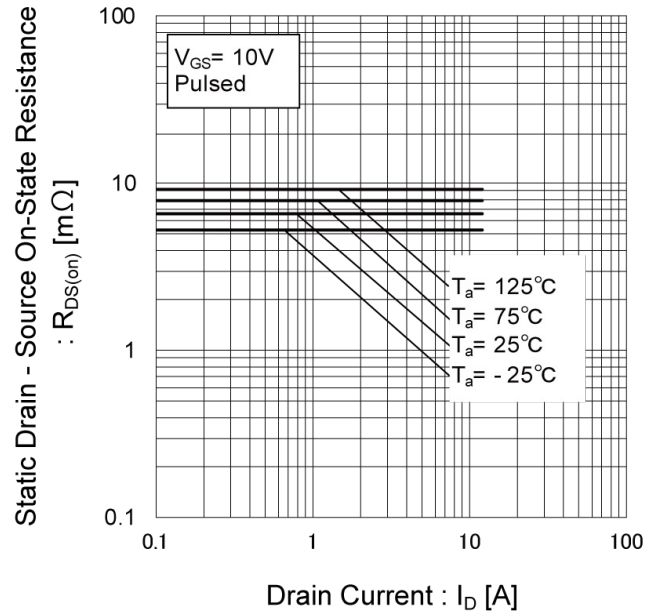
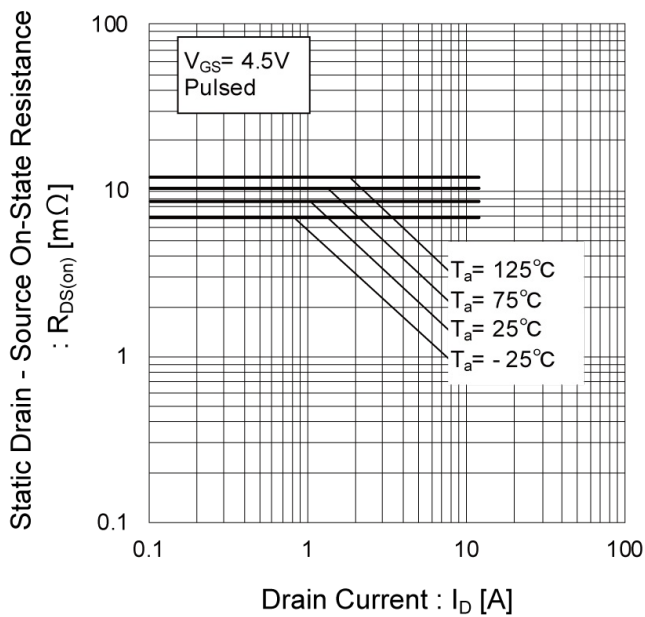


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)





● Electrical characteristic curves

Fig.17 Typical Capacitance vs. Drain - Source Voltage

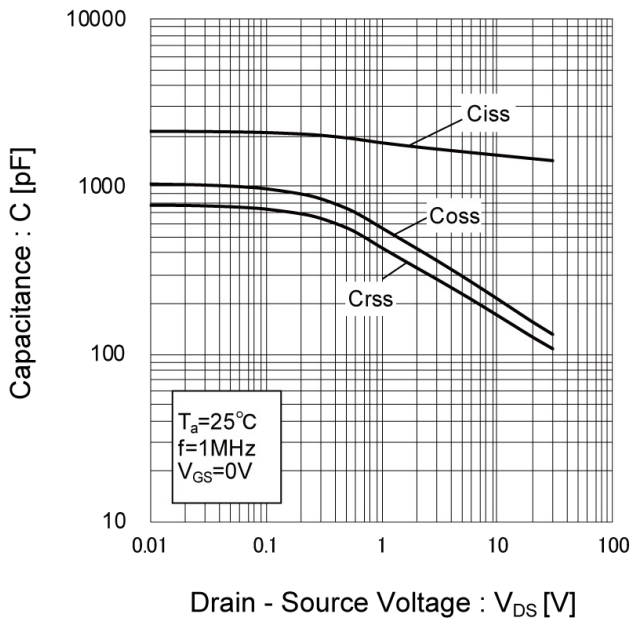


Fig.18 Switching Characteristics

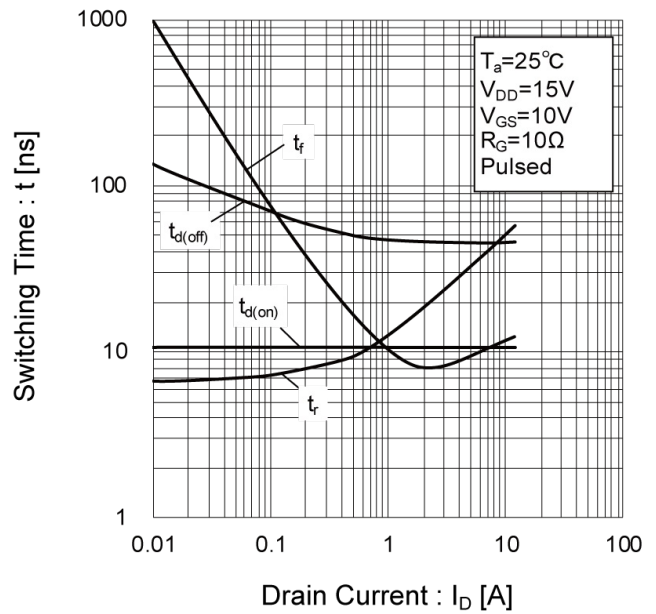


Fig.19 Dynamic Input Characteristics

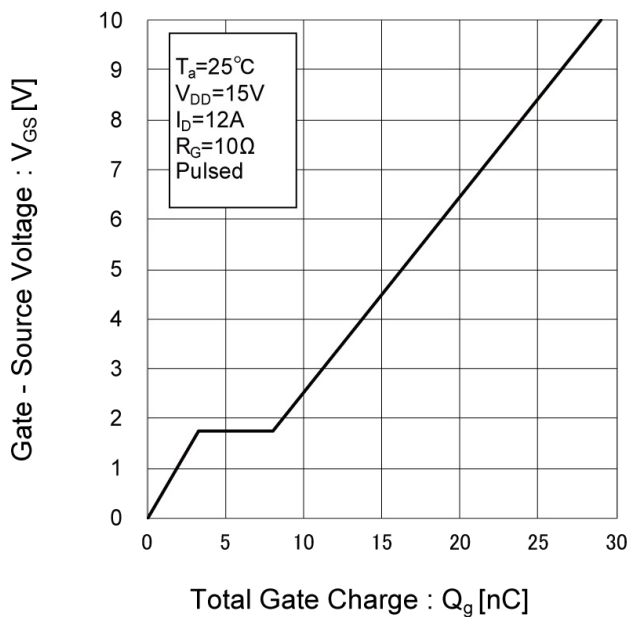
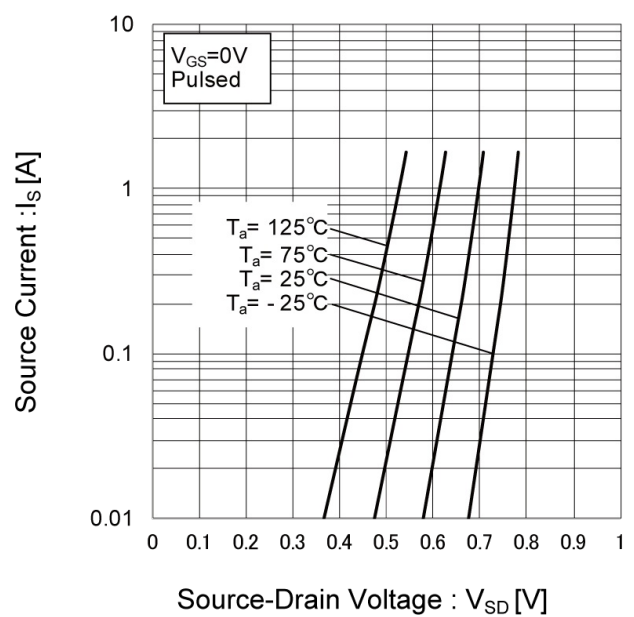


Fig.20 Source Current vs. Source Drain Voltage



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

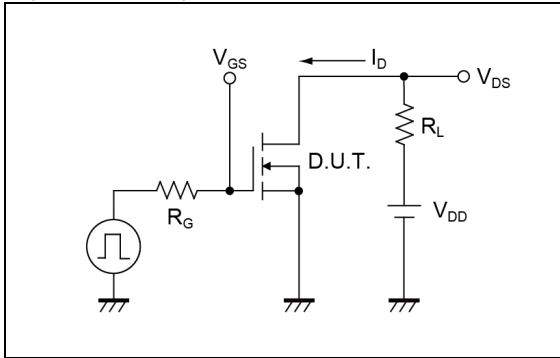


Fig.1-2 Switching Waveforms

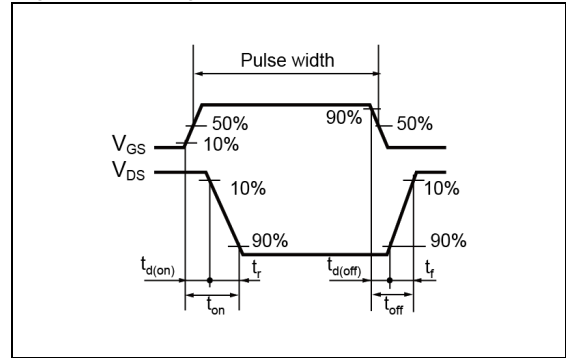


Fig.2-1 Gate Charge Measurement Circuit

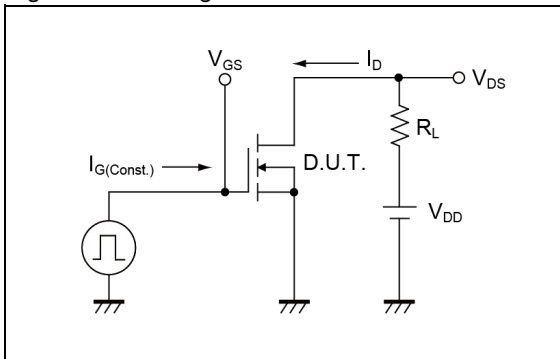
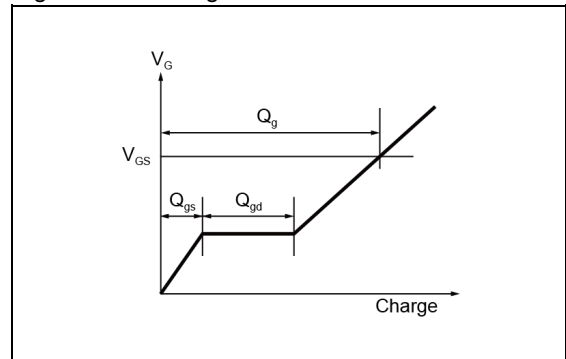


Fig.2-2 Gate Charge Waveform

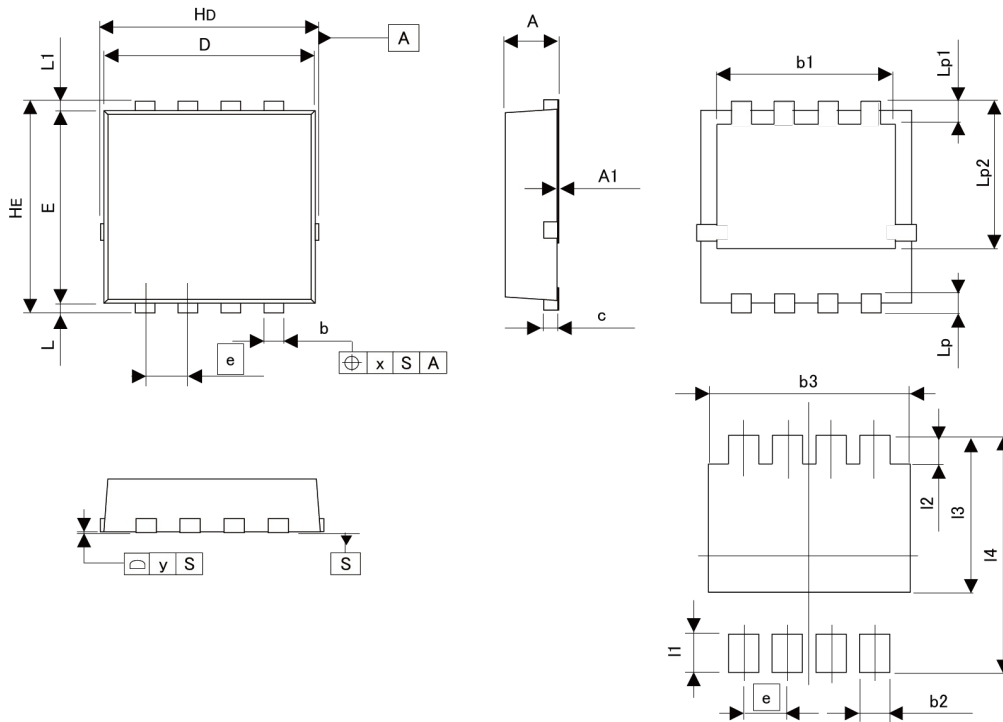


● Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

●Dimensions

HSMT8



Pattern of terminal position areas  
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
A1	0.00	0.05	0.000	0.002
b	0.27	0.37	0.011	0.015
b1	2.50	2.70	0.098	0.106
c	0.10	0.30	0.004	0.012
D	3.10	3.30	0.122	0.130
E	2.90	3.10	0.114	0.122
e	0.65		0.026	
Hd	3.20	3.40	0.126	0.134
HE	3.20	3.40	0.126	0.134
L	0.07	0.25	0.003	0.010
L1	0.07	0.25	0.003	0.010
Lp	0.20	0.40	0.008	0.016
Lp1	0.25	0.45	0.010	0.018
Lp2	2.20	2.40	0.087	0.094
x	-	0.10	-	0.004
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.47	-	0.019
b3	-	2.70	-	0.106
I1	-	0.50	-	0.020
I2	-	0.55	-	0.022
I3	-	2.40	-	0.094
I4	-	3.40	-	0.134

Dimension in mm/inches

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